

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-27 (Canceled).

28. (Previously Presented) A light-emitting device comprising:

a display portion comprising a plurality of pixels formed over a substrate; and

a driver circuit formed over said substrate,

wherein said driver circuit comprises a shift register containing a plurality of flip-flop circuits comprising enhancement-type n-channel thin film transistors and depletion-type n-channel thin film transistors,

wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and

wherein each of said plurality of pixels comprises a light-emitting element.

29. (Previously Presented) A light-emitting device according to claim 28, wherein said substrate is a plastic substrate covered with a protective film.

30. (Canceled)

31. (Previously Presented) A light-emitting device according to claim 28, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile

telephone, and an audio.

32. (Previously Presented) A light-emitting device comprising:

a display portion comprising a plurality of pixels formed over a substrate; and  
a driver circuit formed over said substrate,

wherein said driver circuit comprises a shift register containing a plurality of flip-flop circuits comprising enhancement-type n-channel thin film transistors and depletion-type n-channel thin film transistors, and comprises a plurality of NAND circuits each comprising first and second enhancement-type n-channel thin film transistors and a depletion-type n-channel thin film transistor, wherein a gate electrode of first enhancement-type n-channel thin film transistor is connected to a first output line,

wherein a source electrode of first enhancement-type n-channel thin film transistor is connected to a ground power supply line,

wherein a drain electrode of first enhancement-type n-channel thin film transistor is connected to second enhancement-type n-channel thin film transistor,

wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and

wherein each of said plurality of pixels comprises a light-emitting element.

33. (Previously Presented) A light-emitting device according to claim 32, wherein said substrate is a plastic substrate covered with a protective film.

34. (Canceled)

35. (Previously Presented) A light-emitting device according to claim 32, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

36. (Previously Presented) A light-emitting device comprising:  
a display portion comprising a plurality of pixels formed over a substrate; and  
a driver circuit formed over said substrate,  
wherein each of said plurality of pixels comprises a plurality of enhancement-type n-channel thin film transistors and a plurality of depletion-type n-channel thin film transistors,  
wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and  
wherein each of said plurality of pixels comprises a light-emitting element.

37. (Previously Presented) A light-emitting device according to claim 36, wherein said substrate is a plastic substrate covered with a protective film.

38-39. (Canceled)

40. (Previously Presented) A light-emitting device according to claim 36, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

41. (Previously Presented) A light-emitting device comprising:  
a display portion comprising a plurality of pixels formed over a substrate; and  
a driver circuit formed over said substrate,  
wherein each of said pixels comprises an SRAM formed by a plurality of enhancement-type n-channel thin film transistors and a plurality of depletion-type n-channel thin film transistors,  
wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and  
wherein each of said plurality of pixels comprises a light-emitting element.

42. (Canceled)

43. (Previously Presented) A light-emitting device according to claim 41, wherein said substrate is a plastic substrate covered with a protective film.

44. (Canceled)

45. (Previously Presented) A light-emitting device according to claim 41, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

46. (Previously Presented) A light-emitting device according to claim 28, wherein each of said plurality of flip-flop circuits comprises an enhancement-type n-channel thin film transistor and

two circuits.

47. (Previously Presented) A light-emitting device according to claim 46, wherein one of the circuits is an EEMOS circuit.

48. (Previously Presented) A light-emitting device according to claim 46, wherein one of the circuits is an EDMOS circuit.

49. (Previously Presented) A light-emitting device according to claim 46, wherein each of said plurality of flip-flop circuits further comprises an inverter circuit.

50. (Previously Presented) A light-emitting device according to claim 28, wherein one of the enhancement-type n-channel thin film transistors is electrically connected with one of the depletion-type n-channel thin film transistors.

51. (Previously Presented) A light-emitting device according to claim 46, wherein said plurality of flip-flop circuits are connected in series.

52-56. (Canceled)

57. (Previously Presented) A light-emitting device according to claim 28, wherein a semiconductor element in the display portion has at least two channel forming regions.

58. (Previously Presented) A light-emitting device according to claim 32, wherein a semiconductor element in the display portion has at least two channel forming regions.

59. (Previously Presented) A light-emitting device according to claim 36, wherein a semiconductor element in the display portion has at least two channel forming regions.

60. (Previously Presented) A light-emitting device according to claim 41, wherein a semiconductor element in the display portion has at least two channel forming regions.

61-65. (Canceled)

66. (Previously Presented) A light-emitting device according to claim 28, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

67. (Previously Presented) A light-emitting device according to claim 32, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

68. (Previously Presented) A light-emitting device according to claim 36, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

69. (Previously Presented) A light-emitting device according to claim 41, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

70-73. (Canceled)

74. (Previously Presented) A light-emitting device according to claim 28, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

75. (Previously Presented) A light-emitting device according to claim 32, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

76. (Previously Presented) A light-emitting device according to claim 36, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

77. (Previously Presented) A light-emitting device according to claim 41, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.